Ordering number : EN2406

SANYO No.2406

DFB20T

Diffused Junction Type Silicon Diode

2.0A Power Rectifier

Features

- High-speed switching use
- Reverse recovery time trr = 0.15μs max (B,C,E,G)
  trr = 0.3μs max (J,L)
- Peak reverse voltage V_{RM} = −100 to −1000V
- Average rectified current I_O = 2.0A

Absolute Maximum Ratings at Ta = 25°C

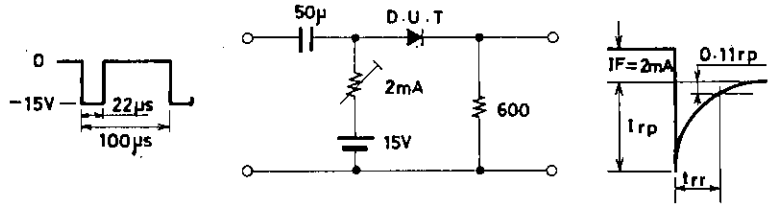
			DFB20TB	DFB20TC	DFB20TE	DFB20TG	unit
Peak Reverse Voltage	V_{RM}		−100	−200	−400	−600	V
Average Rectified Current	I_O	Ta = 40°C	→	→	→	2.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	→	120	A
Junction Temperature	Tj		→	→	→	150	°C
Storage Temperature	Tstg		→	→	−40 to +150		°C

			DFB20TJ	DFB20TL	unit
Peak Reverse Voltage	V_{RM}		−800	−1000	V
Average Rectified Current	I_O	Ta = 40°C	→	2.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	70	A
Junction Temperature	Tj		→	125	°C
Storage Temperature	Tstg		−40 to +150		°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Forward Voltage	V_F	I_F = 2.0A (B,C,E,G)			1.2	V
		I_F = 2.0A (J,L)			1.5	V
Reverse Current	I_R	V_R : At each V_{RM}			−10	μA
Reverse Recovery Time	trr	I_F = 2mA, V_R = −15V (B,C,E,G)			0.15	μs
		I_F = 2mA, V_R = −15V (J,L)			0.3	μs

Reverse Recovery Time Test Circuit



Unit (resistance: Ω, capacitance: F)

Package Dimensions 1177
(unit: mm)